IRHF57133SE (JANSR2N7497T2)

PD-94334E

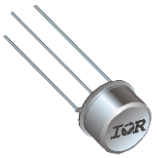
Radiation Hardened Power MOSFET
Thru-Hole TO-205AF (TO-39)
130V, 10.5A, N-channel, R5 Technology

Features

- Single event effect (SEE) hardened
- Ultra low $R_{DS(on)}$
- Identical pre-and post -electrical test conditions
- Repetitive avalanche ratings
- Dynamic dv/dt ratings
- Simple drive requirements
- Hermetically sealed
- ESD rating: Class 1C per MIL-STD-750, Method 1020

Product Summary

- **BV_{DSS}:** 130V
- **I_D :** 10.5A
- **$R_{DS(on),max}$:** 0.1Ω
- **$Q_{G,max}$:** 48nC
- **REF:** MIL-PRF-19500/706



TO-39

Potential Applications

- DC-DC converter
- Motor drives

Product Validation

Qualified to JANS screening flow according to MIL-PRF-19500 for space applications

Description

IR HiRel R5 technology provides high performance power MOSFETs for space applications. These devices have been characterized for Single Event Effects (SEE) with useful performance up to an LET of 80 MeV·cm^2/mg. The combination of low $R_{DS(on)}$ and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well- established advantages of MOSFETs such as voltage control, fast switching and temperature stability of electrical parameters.

Ordering Information

Table 1 Ordering options

Part number	Package	Screening Level	TID Level
IRHF57133SE	TO-205AF (TO-39)	COTS	100 krad(Si)
JANSR2N7497T2	TO-205AF (TO-39)	JANS	100 krad(Si)

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1 Absolute Maximum Ratings

Table 2 Absolute Maximum Ratings (Pre-Irradiation)

Symbol	Parameter	Value	Unit
I_{D1} @ V_{GS} = 12V, T_C = 25°C	Continuous Drain Current	10.5	A
I_{D2} @ V_{GS} = 12V, T_C = 100°C	Continuous Drain Current	6.5	A
I_{DM} @ T_C = 25°C	Pulsed Drain Current [1]	42	A
P_D @ T_C = 25°C	Maximum Power Dissipation	25	W
	Linear Derating Factor	0.2	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy [2]	164	mJ
I_{AR}	Avalanche Current [1]	10.5	A
E_{AR}	Repetitive Avalanche Energy [1]	2.5	mJ
dv/dt	Peak Diode Reverse Recovery [3]	8.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Lead Temperature	300 (0.063 in. /1.6 mm from case for 10s)	
	Weight	0.98 (Typical)	g

[1] Repetitive Rating; Pulse width limited by maximum junction temperature.

[2] V_{DD} = 50V, starting T_J = 25°C, L = 3.0mH, Peak I_L = 10.5A, V_{GS} = 12V

[3] $I_{SD} \leq$ 10.5A, di/dt ≤ 230A/µs, $V_{DD} \leq$ 130V, $T_J \leq$ 150°C

2 Device Characteristics

2.1 Electrical Characteristics (Pre-Irradiation)

Table 3 Static and Dynamic Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	130	—	—	V	V_{GS} = 0V, I_D = 1.0mA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.16	—	V/°C	Reference to 25°C, I_D = 1.0mA
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance	—	—	0.1	Ω	V_{GS} = 12V, I_{D2} = 6.5A [1]
$V_{GS(th)}$	Gate Threshold Voltage	2.5	—	4.5	V	V_{DS} = V_{GS}, I_D = 1mA
Gfs	Forward Transconductance	4.8	—	—	S	V_{DS} = 15V, I_{D2} = 6.5A [1]
I_{DSS}	Zero Gate Voltage Drain Current	—	—	10	µA	V_{DS} = 104V, V_{GS} = 0V
		—	—	25		V_{DS} = 104V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V_{GS} = 20V
	Gate-to-Source Leakage Reverse	—	—	-100		V_{GS} = -20V
Q_G	Total Gate Charge	—	—	48	nC	I_{D1} = 10.5A V_{DS} = 65V V_{GS} = 12V
Q_{GS}	Gate-to-Source Charge	—	—	16		
Q_{GD}	Gate-to-Drain (‘Miller’) Charge	—	—	18		
$t_{d(on)}$	Turn-On Delay Time	—	—	25	ns	I_{D1} = 10.5A ** V_{DD} = 65V R_G = 7.5Ω V_{GS} = 12V
t_r	Rise Time	—	—	100		
$t_{d(off)}$	Turn-Off Delay Time	—	—	35		
t_f	Fall Time	—	—	40		
L_s +L_D	Total Inductance	—	7.0	—	nH	Measured from Drain lead (6mm / 0.25 in from package) to Source lead (6mm/ 0.25 in from package) with Source wire internally bonded from Source pin to Drain pin
C_{iss}	Input Capacitance	—	975	—	pF	V_{GS} = 0V V_{DS} = 25V f = 1.0MHz
C_{oss}	Output Capacitance	—	300	—		
C_{rss}	Reverse Transfer Capacitance	—	20	—		

** Switching speed maximum limits are based on manufacturing test equipment and capability.

[1] Pulse width ≤ 300 µs; Duty Cycle ≤ 2%

2.2 Source-Drain Diode Ratings and Characteristics (Pre-Irradiation)

Table 4 Source-Drain Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	10.5	A	
I_{SM}	Pulsed Source Current (Body Diode) [1]	—	—	42	A	
V_{SD}	Diode Forward Voltage	—	—	1.5	V	T_J = 25°C, I_S = 10.5A, V_{GS} = 0V [2]
t_{rr}	Reverse Recovery Time	—	—	250	ns	T_J = 25°C, I_F = 10.5A, V_{DD} ≤ 25V
Q_{rr}	Reverse Recovery Charge	—	0.9	—	µC	di/dt = 100A/µs [2]
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

2.3 Thermal Characteristics

Table 5 Thermal Resistance

Symbol	Parameter	Min.	Typ.	Max.	Unit
$R_{\theta JC}$	Junction-to-Case	—	—	5.0	°C/W
$R_{\theta JA}$	Junction-to-Ambient (Typical socket mount)	—	175	—	

2.4 Radiation Characteristics

IR HiRel radiation hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at IR HiRel is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 3 and 4) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

2.4.1 Electrical Characteristics — Post Total Dose Irradiation

Table 6 Electrical Characteristics @ T_J = 25°C, Post Total Dose Irradiation [3, 4]

Symbol	Parameter	100 krad (Si)		Unit	Test Conditions
		Min.	Max.		
BV_{DSS}	Drain-to-Source Breakdown Voltage	130	—	V	V_{GS} = 0V, I_D = 1.0mA
$V_{GS(th)}$	Gate Threshold Voltage	2.0	4.5	V	V_{DS} = V_{GS}, I_D = 1.0mA
I_{GSS}	Gate-to-Source Leakage Forward	—	100	nA	V_{GS} = 20V
	Gate-to-Source Leakage Reverse	—	-100		V_{GS} = -20V
I_{DSS}	Zero Gate Voltage Drain Current	—	10	µA	V_{DS} = 104V, V_{GS} = 0V
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance (TO-3) [2]	—	0.08	Ω	V_{GS} = 12V, I_{D2} = 6.5A
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance (TO-39) [2]	—	0.1	Ω	V_{GS} = 12V, I_{D2} = 6.5A
V_{SD}	Diode Forward Voltage	—	1.5	V	V_{GS} = 0V, I_F = 10.5A

[1] Repetitive Rating; Pulse width limited by maximum junction temperature.

[2] Pulse width ≤ 300 µs; Duty Cycle ≤ 2%

[3] Total Dose Irradiation with V_{GS} Bias. V_{GS} = 12V applied and V_{DS} = 0 during irradiation per MIL-STD-750, Method 1019, condition A.

[4] Total Dose Irradiation with V_{DS} Bias. V_{DS} = 104V applied and V_{GS} = 0 during irradiation per MIL-STD-750, Method 1019, condition A.

2.4.2 Single Event Effects — Safe Operating Area

IR HiRel radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. 1 and Table 7.

Table 7 Typical Single Event Effects Safe Operating Area

LET (MeV·cm²/mg)	Energy (MeV)	Range (µm)	V_{DS} (V)				
			V_{GS} = 0V	V_{GS} = -5V	V_{GS} = -10V	V_{GS} = -15V	V_{GS} = -20V
38 ± 5%	300 ± 7.5%	38 ± 7.5%	130	130	130	130	130
61 ± 5%	330 ± 7.5%	31 ± 10%	130	130	130	100	50
84 ± 5%	350 ± 10%	28 ± 7.5%	130	120	30	—	—

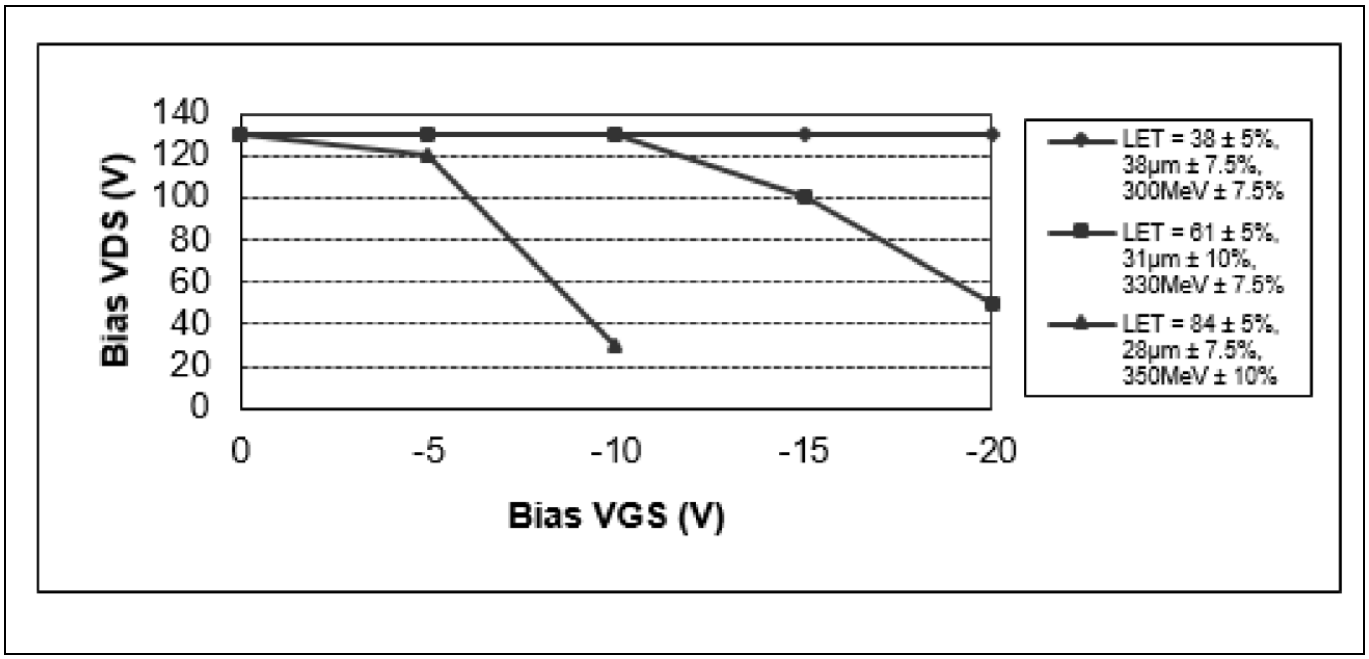


Figure 1 Typical Single Event Effect, Safe Operating Area

3 Electrical Characteristics Curves (Pre-irradiation)

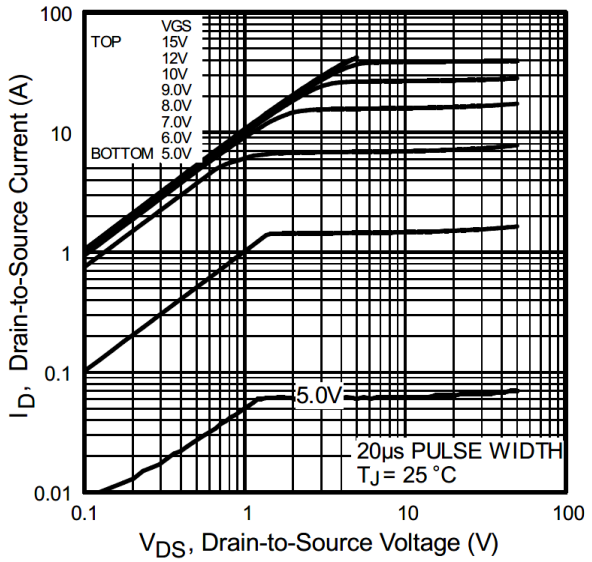


Figure 2 Typical Output Characteristics

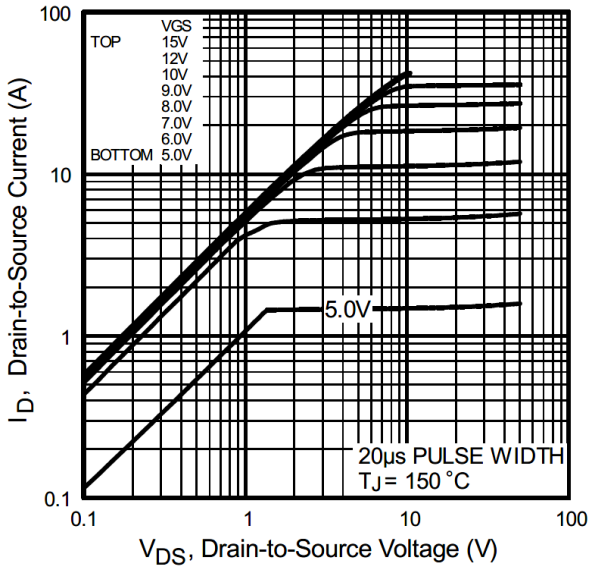


Figure 3 Typical Output Characteristics

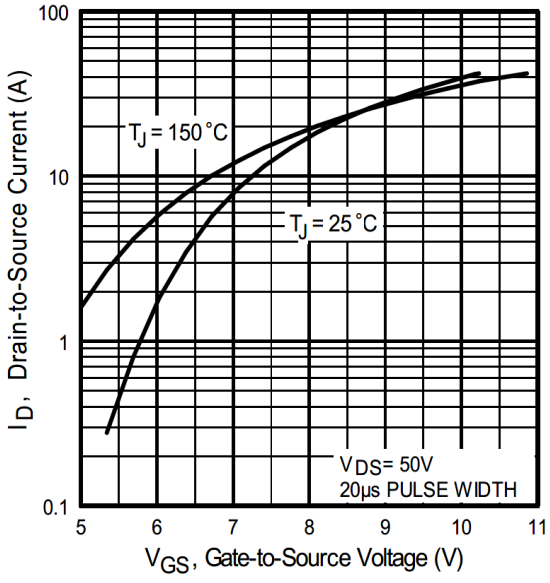


Figure 4 Typical Transfer Characteristics

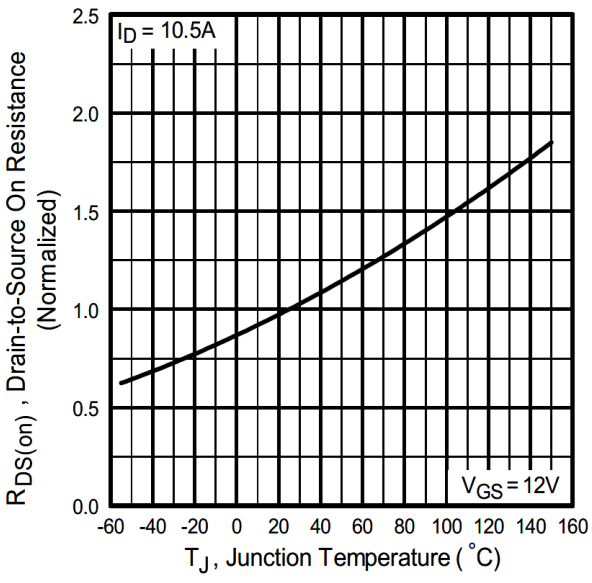


Figure 5 Normalized On-Resistance Vs. Temperature

Electrical Characteristics Curves (Pre-irradiation)

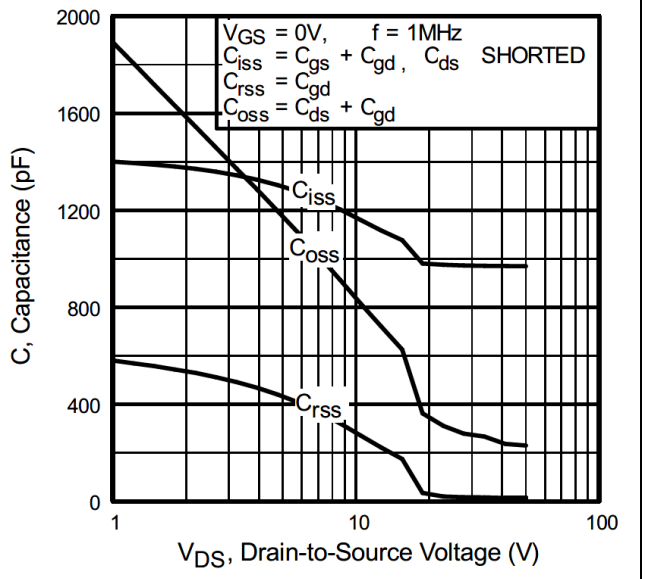


Figure 6 **Typical Capacitance Vs. Drain-to-Source Voltage**

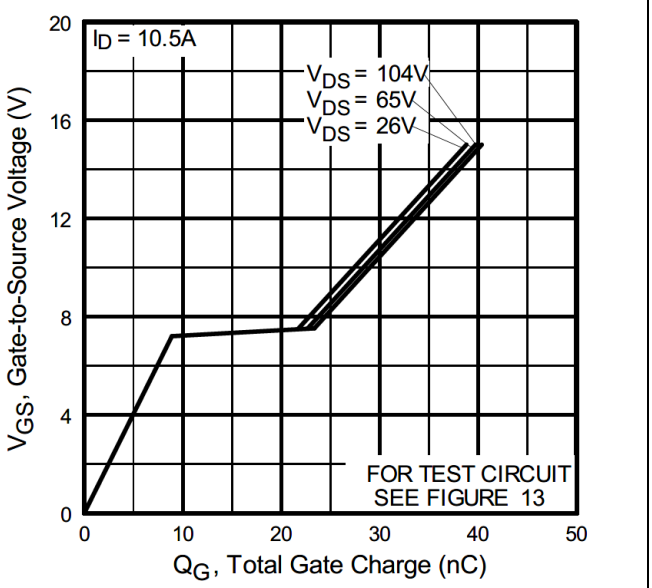


Figure 7 **Typical Gate-to-Source Voltage Vs. Typical Gate Charge**

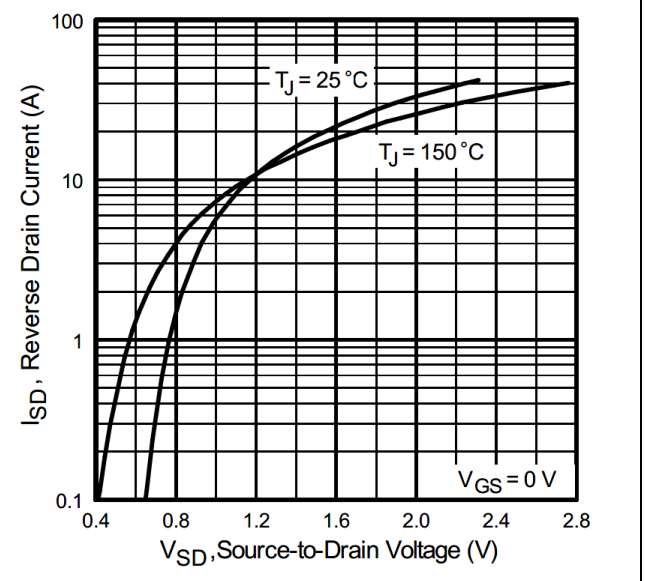


Figure 8 **Typical Source-Drain Current Vs. Diode Forward Voltage**

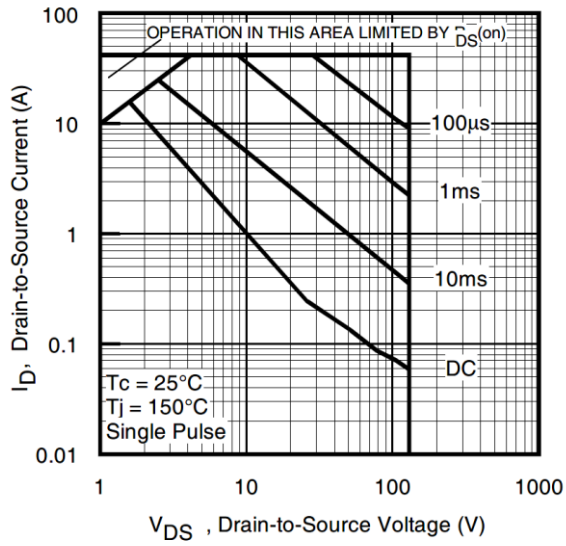


Figure 9 **Maximum Safe Operating Area**

Electrical Characteristics Curves (Pre-irradiation)

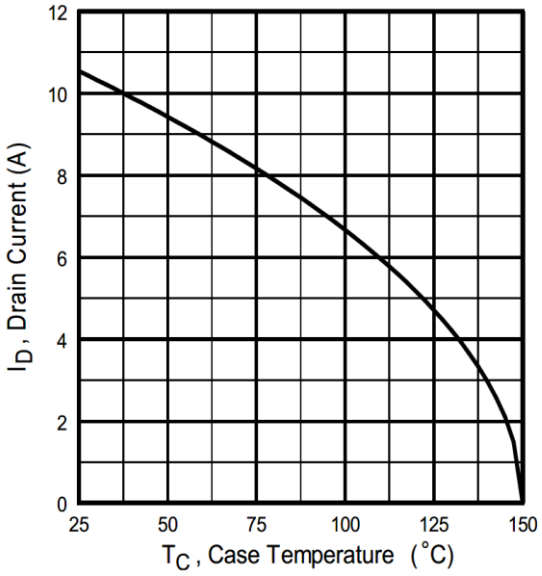


Figure 10 Maximum Drain Current Vs. Case Temperature

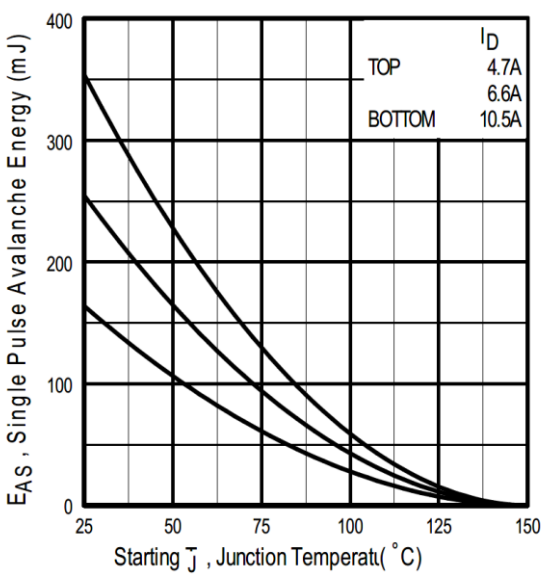


Figure 11 Maximum Avalanche Energy Vs. Junction Temperature

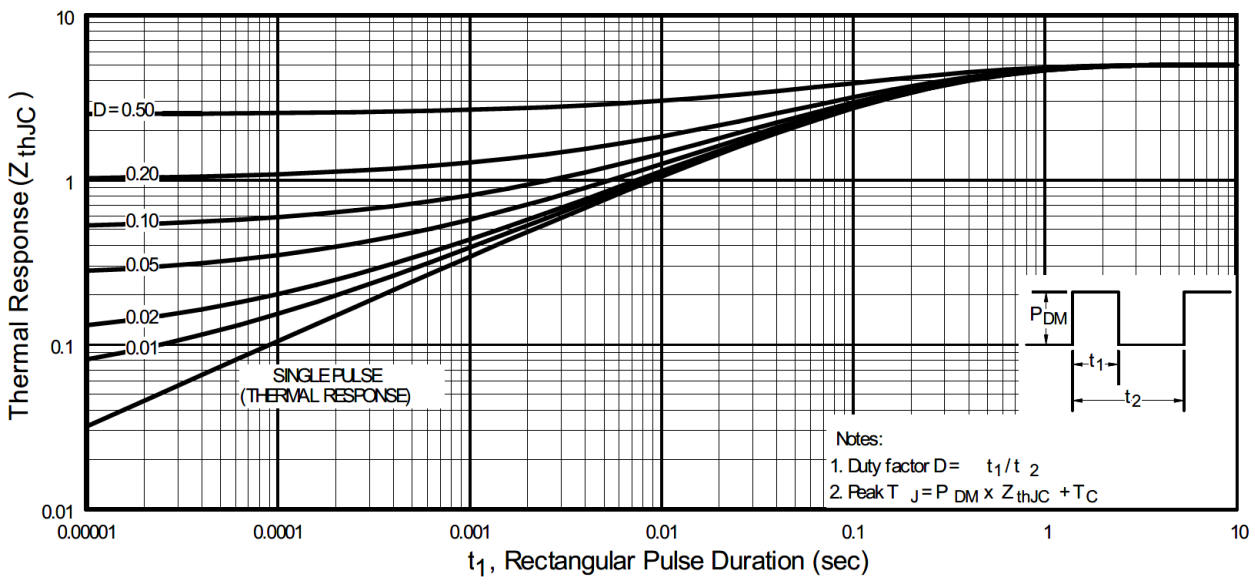


Figure 12 Maximum Effective Transient Thermal Impedance, Junction-to-Case

4 Test Circuits (Pre-irradiation)

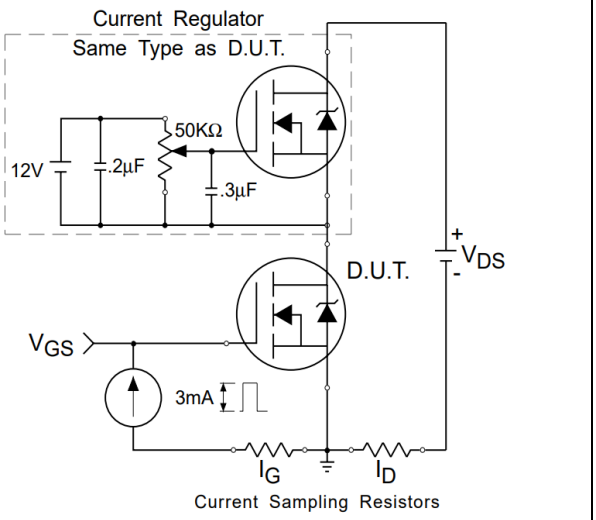


Figure 13 Gate Charge Test Circuit

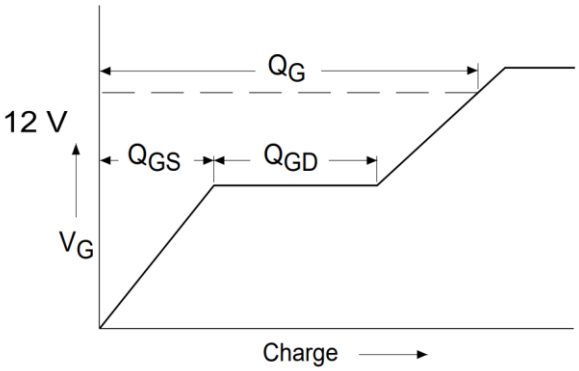


Figure 14 Gate Charge Waveform

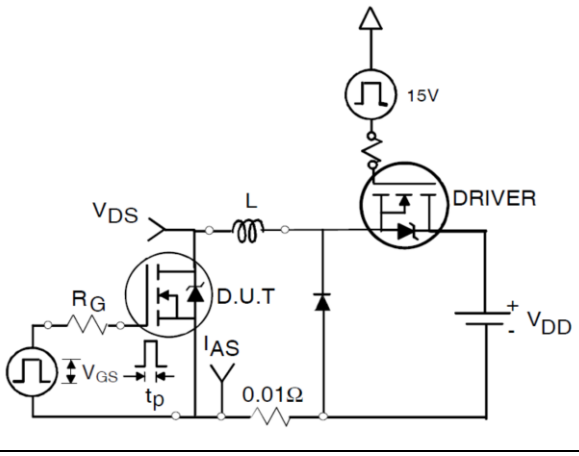


Figure 15 Unclamped Inductive Test Circuit

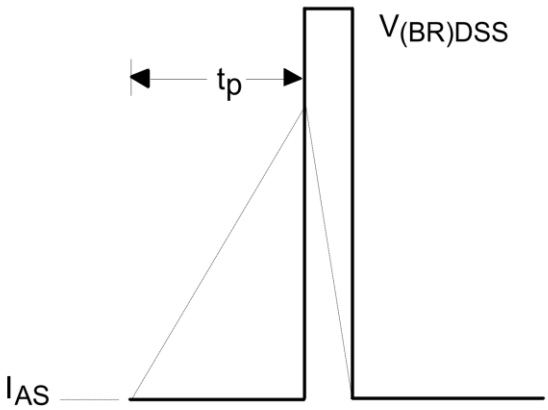


Figure 16 Unclamped Inductive Waveform

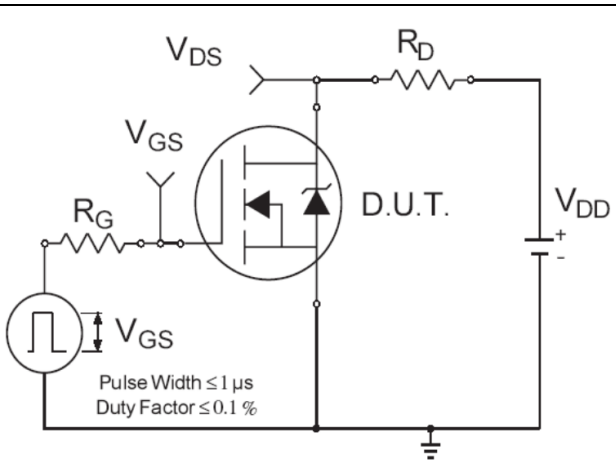


Figure 17 Switching Time Test Circuit

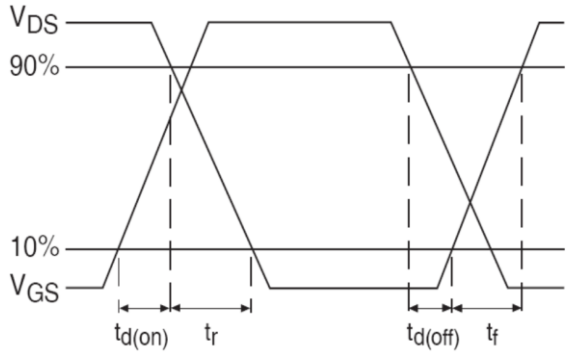
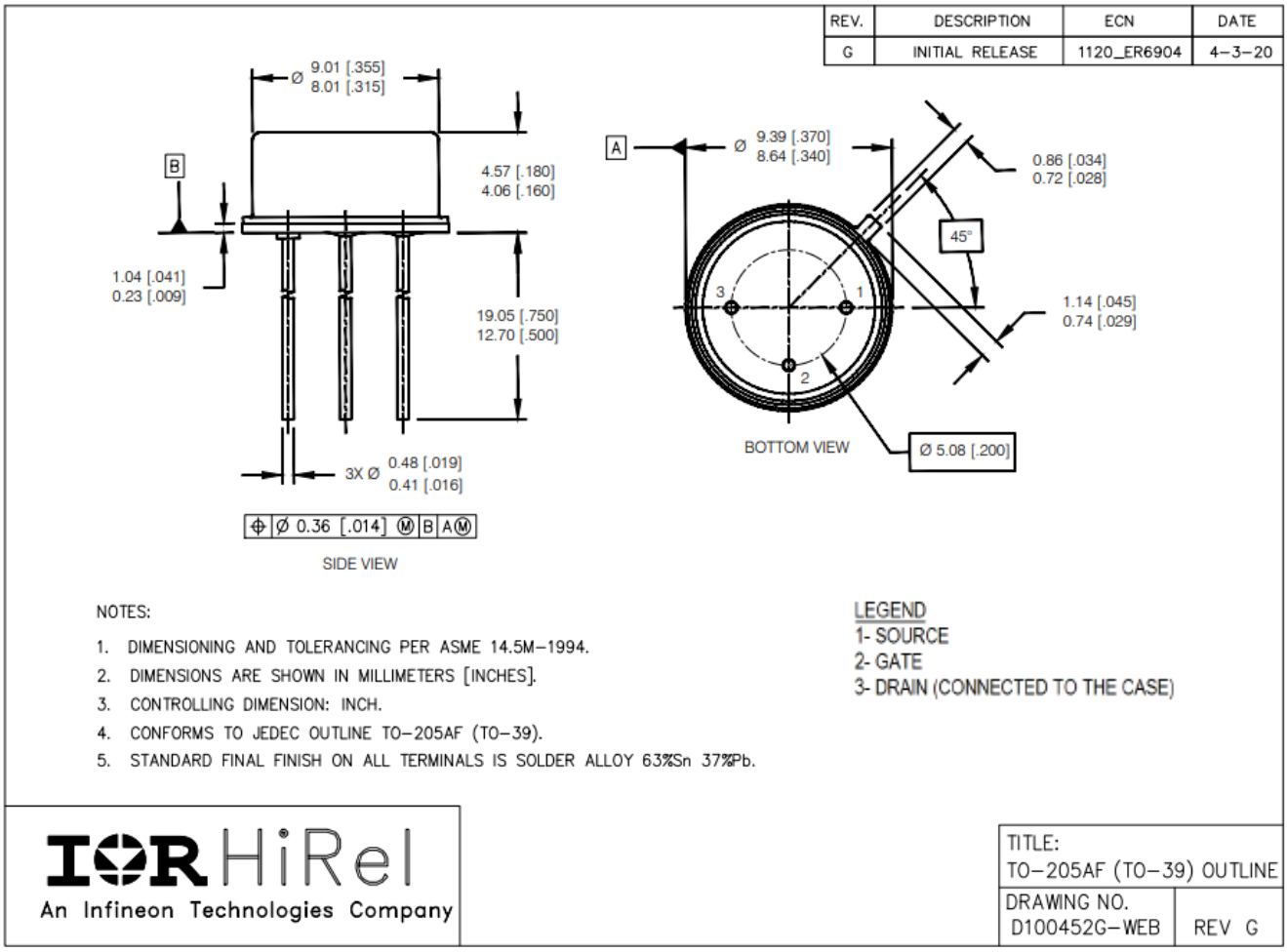


Figure 18 Switching Time Waveforms

5 Package Outline

Note: For the most updated package outline, please see the website: TO-205AF (TO-39)



Revision history

Document version	Date of release	Description of changes
	11/05/2001	Datasheet (PD-94334)
Rev A	01/07/2002	Updated switch time
Rev B	06/16/2004	Added QPL Part Number
Rev C	07/25/2018	Updated based on ECN-1120_05934
Rev D	11/10/2020	Updated based on ECN-1120_08235
Rev E	01/30/2025	Updated based on ECN-Z8F80742840

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